

IN THE CLAIMS:

Please amend the claims as follows:

1. (Previously Presented) A film deposition method comprising:
 - a first step of preparing a fluid that has organic metal as a main component which precipitates a film deposition material using pyrolytic decomposition, wherein the fluid comprises an aliphatic saturated hydrocarbon solvent and the organic metal is a copper diketonate;
 - a second step of applying the fluid onto a to-be-processed body at a temperature within the non-reactive range of the organic metal; and
 - a third step of heating the to-be-processed body to a second temperature, and causing a pyrolytic decomposition reaction of the organic metal throughout the fluid that is applied onto the to-be-processed body to occur to form a copper film on the to-be-processed body.
6. (Previously Presented) The film deposition method in claim 1, wherein the to-be-processed body is a semiconductor wafer.
11. (Currently Amended) A film deposition method comprising:
 - a first step of preparing a fluid that has organic metal as a main component which precipitates a film deposition material using pyrolytic decomposition, wherein the organic metal is selected from the group consisting of (hfac)Cu(tmvs) and ~~(hfac)Cu()~~ (hfac)Cu(teovs) and the fluid further comprises an aliphatic saturated hydrocarbon solvent;
 - a second step of applying the fluid onto a to-be-processed body at a temperature within the non-reactive range of the organic metal; and
 - a third step of heating the to-be-processed body to a second temperature, and causing a pyrolytic decomposition reaction of the organic metal throughout the fluid that is applied onto the to-be-processed body to occur to form a copper film on the to-be-processed body.

12. (Previously Presented) The film deposition method in claim 11, wherein the to-be-processed body is a semiconductor wafer.
13. (Previously Presented) A film deposition method comprising:
a first step of preparing a fluid that has organic metal as a main component which precipitates a film deposition material using pyrolytic decomposition, wherein the fluid further comprises an aliphatic saturated hydrocarbon solvent;
a second step of applying the fluid onto a to-be-processed body at a temperature within the non-reactive range of the organic metal; and
a third step of heating the to-be-processed body to a second temperature, and causing a pyrolytic decomposition reaction of the organic metal throughout the fluid that is applied onto the to-be-processed body to occur to form a film on the to-be-processed body.
14. (Previously Presented) The film deposition method in claim 13, wherein the organic metal is a copper diketonate.
15. (Previously Presented) The film deposition method in claim 14, wherein the copper diketonate is selected from the group consisting of (hfac)Cu(tmvs) and (hfac)Cu(teovs).
16. (Previously Presented) The film deposition method in claim 15, wherein copper is deposited as a film.
17. (Previously Presented) The film deposition method in claim 16, wherein the to-be-processed body is a semiconductor wafer.